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NOV 28 2001

TECHNOLOGY CENTER 2800

November 28, 2001

Time: 2:30 pm
(Minneapolis, Minn.)

TO: Commissioner for Patents
Attn: Mark V. Prenty
Patent Examining Corps
Facsimile Center
Washington, D.C. 20231

FROM: David C. Peterson

OUR REF: 303.229US2

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* Please deliver to Examiner Mark V. Prenty in Art Unit 2822. *

Document(s) Transmitted: An Amendment and Response Under 1.116 (6 pgs.) and a Clean Verison
f Pending Claims (4 pgs.)

Total pages of this transmission, including cover letter: 11 pgs

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In re. Patent Application of: Leonard Forbes

Examiner: Mark V. Prenty

Serial No.: 09/132,157


Group Art Unit: 2822

Filed: August 11, 1998

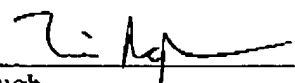
Docket No.: 303.229US2

Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION
IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH

Please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

By: 
Name: David C. Peterson
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Tina M. Pugh

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EXPEDITED PROCEDURE - EXAMINING GROUP 2822

S/N 09/132.157PATENTIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

| | | | |
|-------------|---|-----------------|----------------|
| Applicant: | Leonard Forbes | Examiner: | Mark V. Prenty |
| Serial No.: | 09/132,157 | Group Art Unit: | 2822 |
| Filed: | August 11, 1998 | Docket: | 303.229US2 |
| Title: | SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH | | |

AMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116

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In response to the final Office Action mailed September 25, 2001, please amend the application as follows: TECHNOLOGY CENTER 2800

IN THE CLAIMS

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect amendment of previously pending claims 11, 24, 25, 28, 38, 40, and 41. The specific amendments to individual claims are detailed in the following marked up set of claims.

11. (Six times amended) A p-channel metal-oxide-semiconductor transistor, comprising:
- a silicon substrate;
 - a silicon dioxide (SiO₂) gate oxide, coupled to the substrate;
 - a gate, coupled to the SiO₂ gate oxide;
 - source/drain regions formed in the substrate on opposite sides of the gate; and
 - a Si_{1-x}Ge_x channel region, having a germanium molar fraction x, located underneath the SiO₂ gate oxide and between the source/drain regions, wherein x is less than or equal to 0.6, and wherein the Si_{1-x}Ge_x channel region forms a continuous Si_{1-x}Ge_x/SiO₂ gate oxide interface wherein no germanium oxide is present at the Si_{1-x}Ge_x/SiO₂ gate oxide interface as a result of ion implantation of germanium through the previously formed SiO₂ gate oxide.